

QSI LASER DIODE SPECIFICATIONS FOR APPROVAL

Customer :.

Model : QL67D6S-A/B/C

Signature of Approval

Approved by _____

Checked by _____

Issued by _____

Approval by Customer



QSI Co., Ltd.

315-9, Cheonheung-ri, Sungger-eup,
Cheonan-city, Chungnam, Korea 330-836

WWW.QSILaser.com

QL67D6S-A/B/C

InGaAIP Laser Diode

Quantum Semiconductor International Co., Ltd.

Ver. 0 JAN. 2004

◆ OVERVIEW

QL67D6S-A/B/C is a MOCVD grown 670nm band **Gain-Guided** type *InGaAIP* laser diode with quantum well structure. It's an attractive light source, with a typical light output power of 5mW for optoelectronic devices such as Bar Code Reader.

◆ APPLICATION

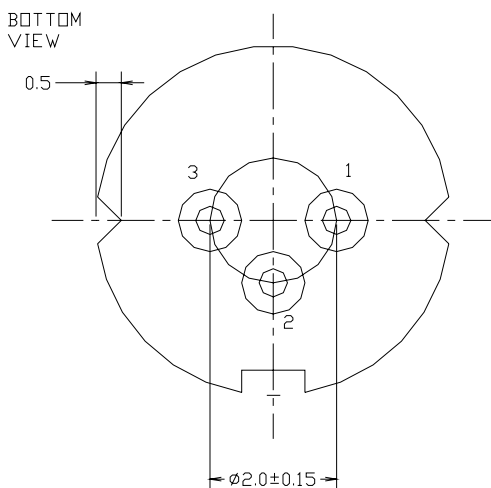
- Optical Leveler
- Laser Module
- Bar Code Reader

◆ FEATURES

- Visible Light Output : $\lambda_p = 670 \text{ nm}$
- Optical Power Output : 5mW CW
- Package Type : TO-18 (5.6mm ϕ)
- Built-in Photo Diode for Monitoring Laser Diode

◆ ELECTRICAL CONNECTION

Bottom View



Pin Configuration

| | |
|---|-------------------------------|
| A | LD cathode, PD anode (Fig. 1) |
| B | LD , PD anode (Fig. 2) |
| C | LD anode, PD cathode (Fig. 3) |

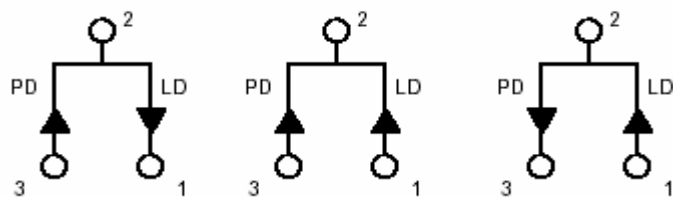


Fig. 1

QL67D6SA

Fig. 2

QL67D6SB

Fig. 3

QL67D6SC

◆ ABSOLUTE MAXIMUM RATING at Tc=25°C

| Items | Symbols | Values | Unit |
|-----------------------------|---------|-----------|------|
| Optical Output Power | P | 7 | mW |
| Laser Diode Reverse Voltage | V | 2 | V |
| Photo Diode Reverse Voltage | V | 30 | V |
| Operating Temperature | Topr | -10 ~ +60 | °C |
| Storage Temperature | Tstg | -40 ~ +85 | °C |

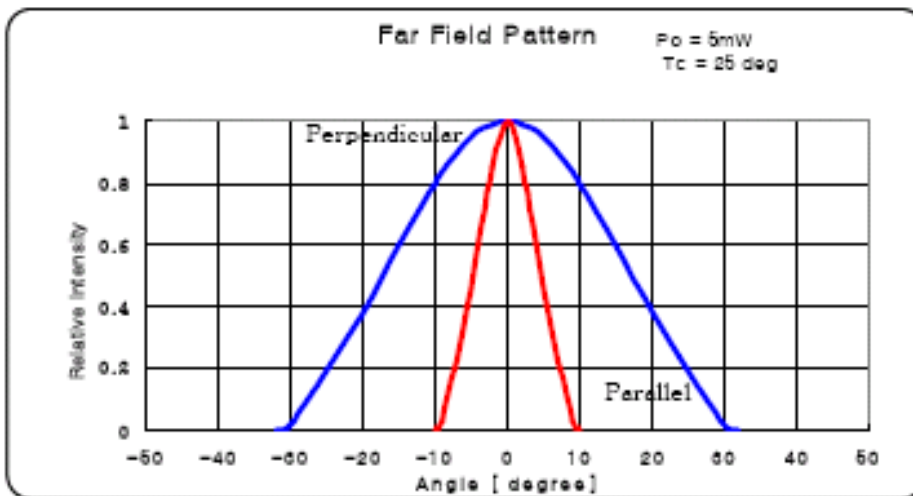
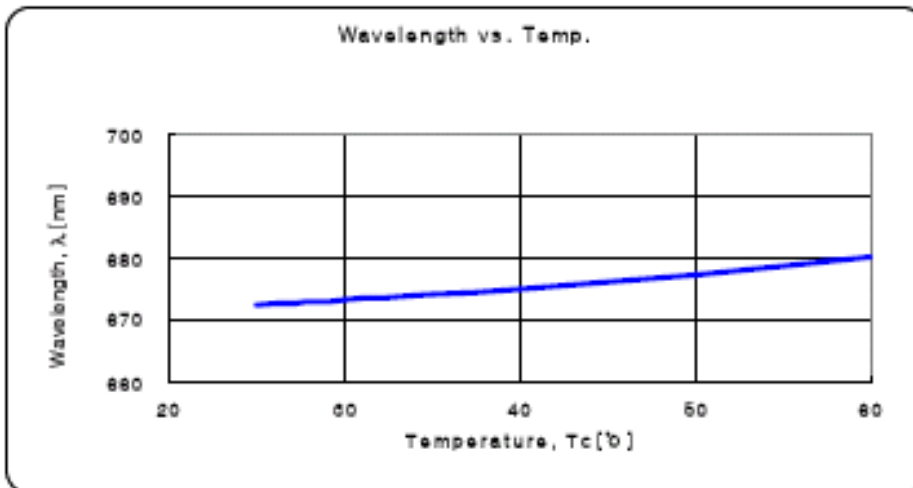
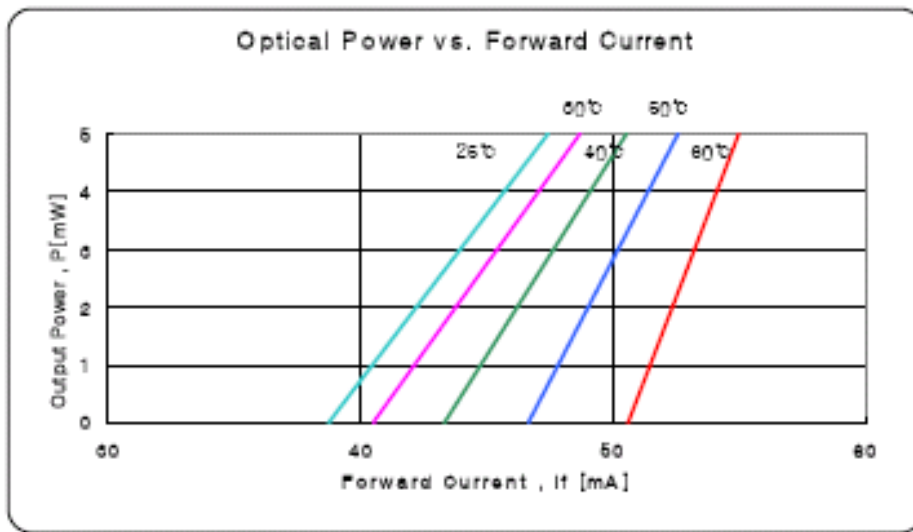
◆ ELECTRICAL and OPTICAL CHARACTERISTICS at Tc=25°C

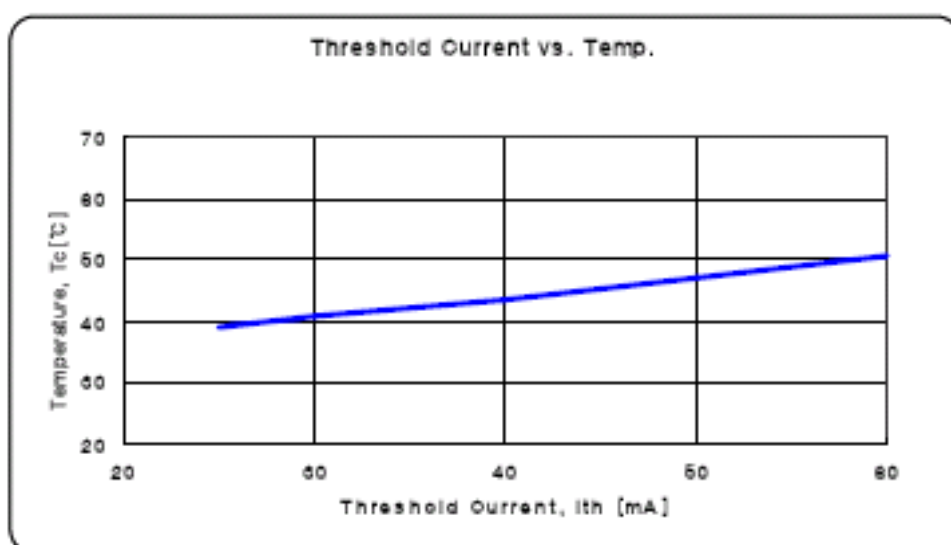
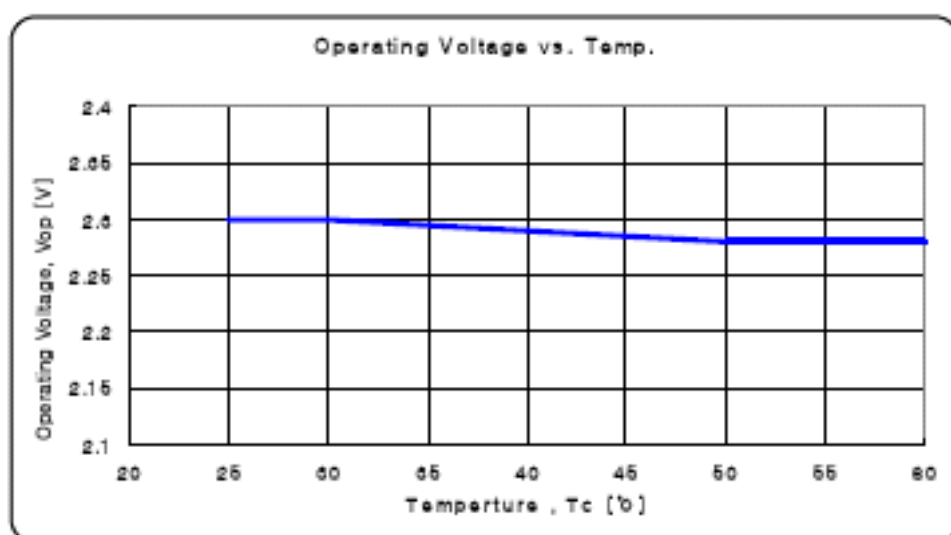
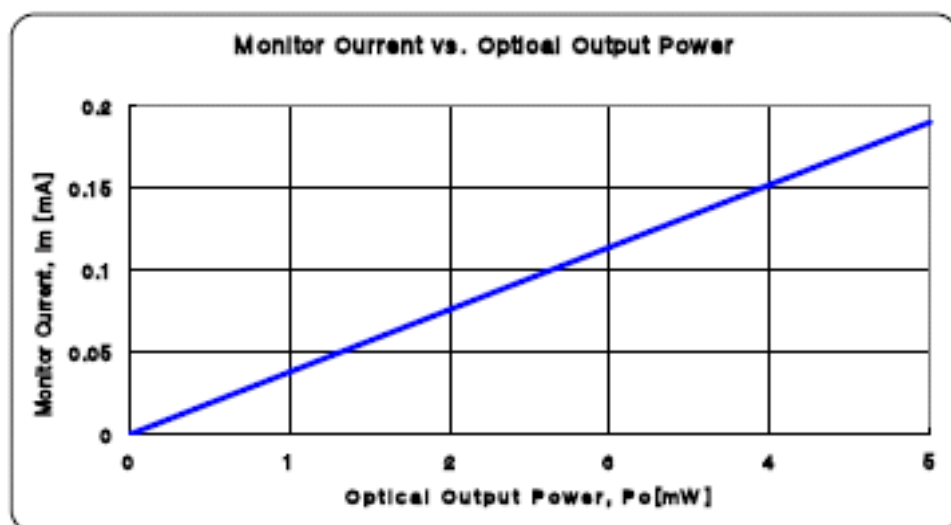
| Items | Symbols | Min. | Typ. | Max. | Unit | Condition |
|----------------------|--------------------------------|------|------|-----------|---------------|-----------|
| Optical Output Power | Po | - | 5 | - | mW | - |
| Threshold Current | Ith | - | 40 | 60 | mA | - |
| Operating Current | Iop | - | 50 | 70 | mA | Po=5mW |
| Operating Voltage | Vop | - | 2.3 | 2.6 | V | Po=5mW |
| Lasing Wavelength | λ_p | 660 | 670 | 680 | nm | Po=5mW |
| Beam Divergence | $\theta_{ }$ | 8 | 11 | 15 | deg | Po=5mW |
| | θ_{\perp} | 24 | 32 | 35 | deg | Po=5mW |
| Beam Angle | $\Delta\theta_{ }$ | - | - | ± 1.5 | deg | Po=5mW |
| | $\Delta\theta_{\perp}$ | - | - | ± 2.5 | deg | Po=5mW |
| Monitor Current | I _m | 0.1 | 0.2 | 0.5 | mA | Po=5mW |
| Astigmatism | As | | 30 | | μm | |
| Optical Distance | $\Delta X, \Delta Y, \Delta Z$ | - | - | ± 60 | μm | - |

NOTICE : QL67D6S-A/B/C to be operated on APC

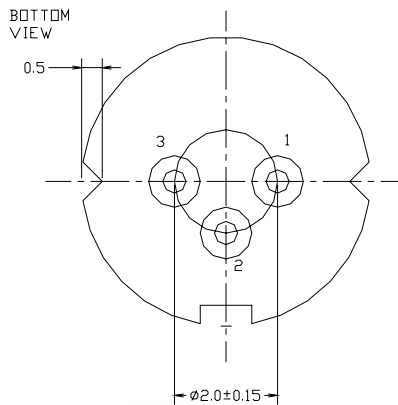
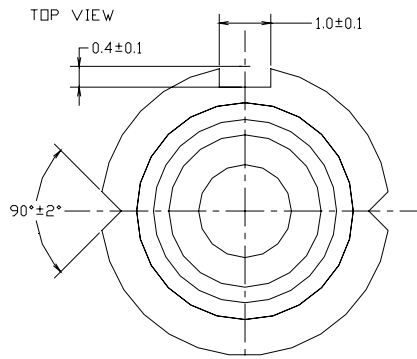
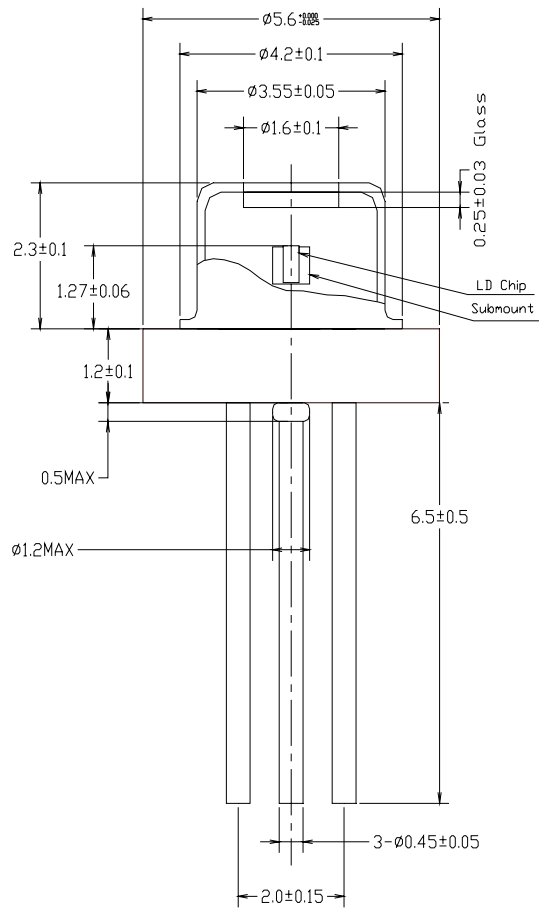
The above product specifications are subject to change without notice.

◆ EXAMPLE of REPRESENTATIVE CHARACTERISTICS





◆ PACKAGE DIMENSION



◆PACKING

